TOSHIBA BIPOLAR DIGITAL INTEGRATED CIRCUIT SILICON MONOLITHIC

TD62308AP,TD62308F,TD62308AF

4CH LOW INPUT ACTIVE HIGH-CURRENT DARLINGTON SINK DRIVER

The TD62308AP/F/AF is a non–inverting transistor array which is comprised of four NPN darlington output stages and PNP input stages.

This device is low–level input active driver and is suitable for operation with 5–V TTL, 5–V CMOS and 5–V Microprocessor which have sink current output drivers.

Application include relay, hammer, lamp and stepping motor drivers.

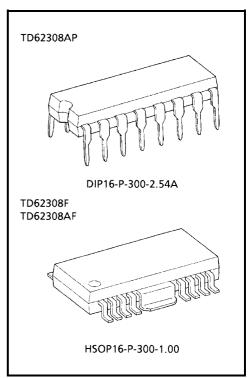
FEATURES

- Output current (single output) 1.5 A (Max)
- High sustaining voltage output 35 V (Min) (TD62308F)

50 V (Min)

(TD62308AP, TD62308AF)

- Output clamp diodes
- Input compatible with TTL and 5 V CMOS
- Low level active inputs
- Standard supply voltage
- Two VCC terminals VCC1, VCC2 (separated)
- GND and SUB terminal = heat sink
- Package type-AP : DIP-16 pin
- Package type-F, AF: HSOP-16 pin

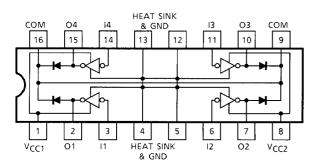


Weight

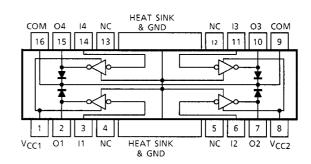
DIP16-P-300-2.54A : 1.11 g (Typ.) HSOP16-P-300-1.00 : 0.50 g (Typ.)

PIN CONNECTION (TOP VIEW)

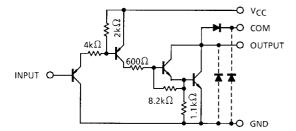
TD62308AP



TD62308F, TD62308AF



SCHEMATICS (EACH DRIVER)



Note: The input and output parasitic diodes cannot be used as clamp diodes.

PRECAUTIONS for USING

- (1) This IC does not include built-in protection circuits for excess current or overvoltage. If this IC is subjected to excess current or overvoltage, it may be destroyed. Hence, the utmost care must be taken when systems which incorporate this IC are designed. Utmost care is necessary in the design of the output line, VCC, COMMON and GND line since IC may be destroyed due to short-circuit between outputs, air contamination fault, or fault by improper grounding.
- (2) If a TD62308AP/F/AF is being used to drive an inductive load (such as a motor, solenoid or relay), Toshiba recommends that the diodes (pins 9 and 16) be connected to the secondary power supply pin so as to absorb the counter electromotive force generated by the load. Please adhere to the device's maximum ratings. Toshiba recommends that zener diodes be connected between the diodes (pins 9 and 16) and the secondary power supply pin (as the anode) so as to enable rapid absorption of the counter electromotive force. Again, please adhere to the device's maximum ratings.

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MAXIMUM RATINGS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT		
Supply Voltage	V _{CC}	-0.5~10	V		
Output Sustaining Voltage	F	\/	-0.5~35	V	
	AP, AF	V _{CE} (SUS)	-0.5~50		
Output Current	l _{OUT}	1.5	A / ch		
Input Current	I _{IN}	-10	mA		
Input Voltage	V _{IN}	-0.5~30	V		
Clamp diode Reverse Voltage	F	V_{R}	35	V	
	AP, AF	VR	50	V	
Clamp Diode Forward Current	I _F	1.5	Α		
Power Dissipation	AP	D-	1.47 / 2.7 (Note 1)	W	
	F, AF	P _D	0.9 / 1.4 (Note 2)		
Operating Temperature	T _{opr}	-40~85	°C		
Storage Temperature	T _{stg}	-55~150	°C		

Note 1: On Glass Epoxy PCB (50 × 50 × 1.6 mm Cu 50%)

Note 2: On Glass Epoxy PCB (60 × 30 × 1.6 mm Cu 50%)



RECOMMENDED OPERATING CONDITIONS (Ta = $-40 \sim 85$ °C)

CHARACTERISTIC		SYMBOL	CONDITION		MIN	TYP.	MAX	UNIT	
Supply Voltage		V _{CC}	_		4.5	_	5.5	٧	
Output Sustaining Voltage	F	V _{CE} (SUS)	_		0	_	35	V	
	AP, AF		_		0	_	50		
	•		DC 1 circuit, Ta = 25°C		0	_	1250		
Output Current	AP	Іоит	T_{pw} = 25 ms 4 circuits Ta = 85°C T _j = 120°C	Duty = 10%	0	_	1250	mA / ch	
				Duty = 50%	0	_	700		
	F, AF			Duty = 10%	0	_	1250		
				Duty = 50%	0	_	390		
Input Voltage		V _{IN}	_		0	_	25	V	
Input Voltage	Output On	V _{IN (ON)}	_		0	_	V _{CC} -3.6	- v	
	Output Off	V _{IN (OFF)}	-		V _{CC} -1.0	_	V _{CC}		
Clamp Diode Reverse Voltage	F	1/	_		_	_	35	· V	
	AP, AF	V_{R}	_		_	_	50		
Clamp Diode Forward Current		I _F	_		_	_	1.25	Α	
Power Dissipation	AP	D-	Ta = 85°C	(Note 1)	_	_	1.4	w	
	F, AF	P_{D}	Ta = 85°C	(Note 2)	_	_	0.7] ^{vv}	

Note 1: On Glass Epoxy PCB ($50 \times 50 \times 1.6$ mm Cu 50%) Note 2: On Glass Epoxy PCB ($60 \times 30 \times 1.6$ mm Cu 50%)

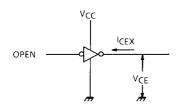
ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC		SYMBOL	TEST CIR- CUIT	TEST CONDITION		MIN	TYP.	MAX	UNIT
Output Leakage Current	AP, AF	I _{CEX}	1	V _{CE} = 50 V, Ta = 25°C		_	_	50	μΑ
				V _{CE} = 50 V	_	_	100		
	F			V _{CE} = 35 V, Ta = 25°C		_	_	50	
				V _{CE} = 35 V, Ta = 85°C		_	_	100	
Output Saturation Voltage		V _{CE} (sat)	3	I _{OUT} = 1.25	_	_	1.8	٧	
				I _{OUT} = 0.7 A		_	_		1.3
Input Voltage	"H" Level	V_{IH}		- –		V _{CC} -1.6	_	25	V
	"L" Level	V_{IL}	_		_	_	_	V _{CC} -3.6	V
Input Current	"H" Level	I _{IH}				_	_	10	μΑ
	"L" Level	I _{IL}		_		_	-0.05	-0.36	mA
Clamp Diode Reverse Current	AP, AF	I_	4	V _R = 50 V, Ta = 25°C		_	_	50	
	F	I _R		V _R = 35 V, Ta = 25°C		_	_	50	μA
Clamp Diode Forward Voltage		V _F	5	I _F = 1.25 A		_	1.5	2.0	V
Supply Current	Output On	I _{CC (ON)}	2	V _{CC} = 5.5 V, V _{IN} = 0 V		_	8.5	12.5	mA / ch
Supply Current	Output Off	I _{CC (OFF)}	_	V_{CC} = 5.5 V, V_{IN} = V_{CC}		_	_	1.0	μA
Turn-On Delay	F		- 6	C _L = 15 pF	V _{OUT} = 35 V R _L = 28 Ω		0.2	_	- μs
	AP, AF	t _{ON}			V _{OUT} = 50 V R _L = 40 Ω		0.2		
Turn-Off Delay	F	tou	O		V _{OUT} = 35 V R _L = 28 Ω		5.0		
	AP, AF	t _{ON}			V _{OUT} = 35 V R _L = 40 Ω				

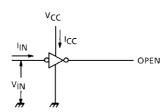
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TEST CIRCUIT

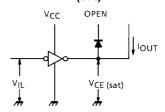
1. ICEX



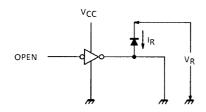
2. Icc



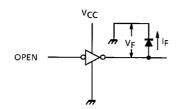
3. VCE (sat)



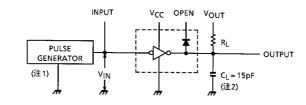
4. IR

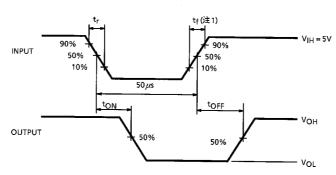


5. V_F



6. ton, toff

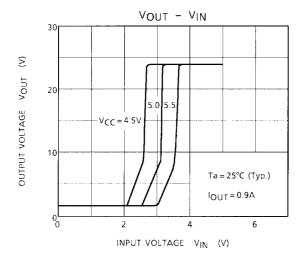


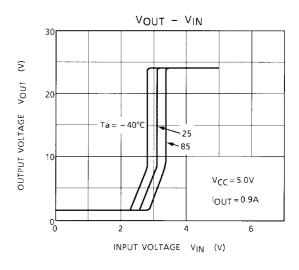


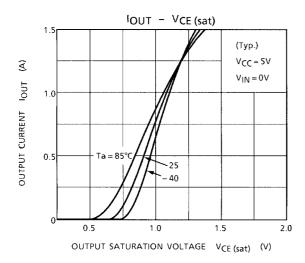
Note 1: Pulse width 50 μ s, duty cycle 10%

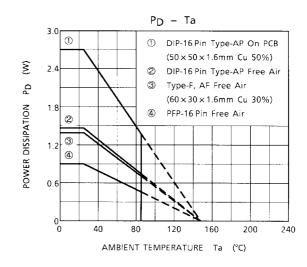
Output impedance 50 Ω tr \leq 5 ns, tf \leq 10 ns

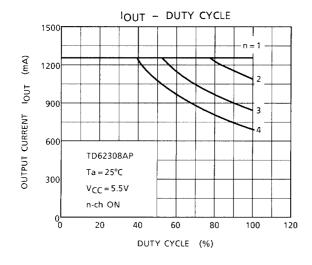
Note 2: CL includes probe and jig capacitance.

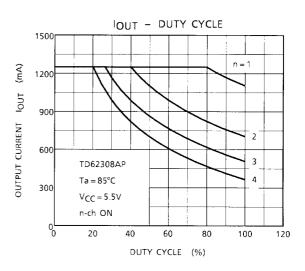




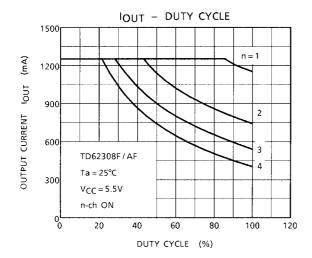


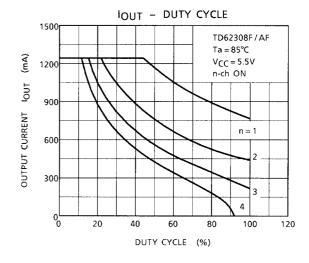






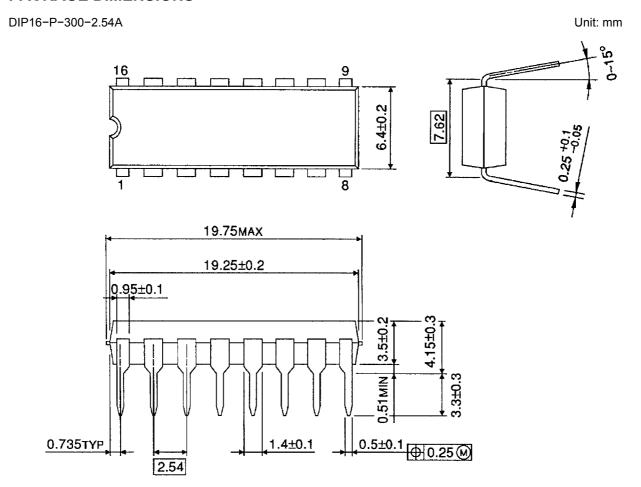
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PACKAGE DIMENSIONS

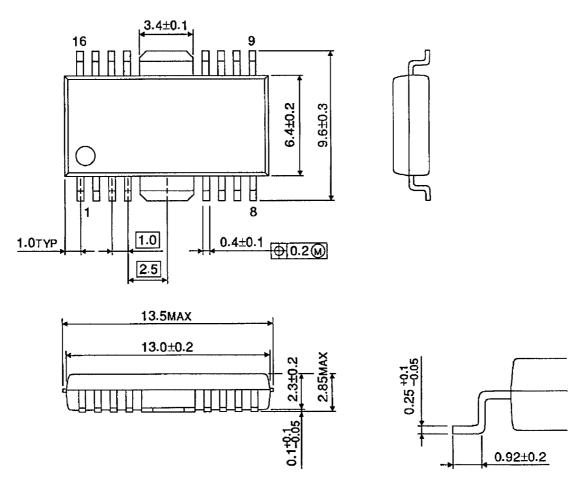


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Weight: 1.11 g (Typ.)

PACKAGE DIMENSIONS

HSOP16-P-300-1.00 Unit: mm



Weight: 0.50 g (Typ.)

RESTRICTIONS ON PRODUCT USE

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